

Title (en)

Active matrix type semiconductor display device

Title (de)

Halbleiteranzeigeeinrichtung mit aktiver Matrix

Title (fr)

Dispositif d'affichage à semi-conducteurs du type à matrice active

Publication

**EP 1003151 A3 20011121 (EN)**

Application

**EP 99122790 A 19991116**

Priority

- JP 32647098 A 19981117
- JP 8620299 A 19990329

Abstract (en)

[origin: EP1003151A2] There is provided an active matrix type semiconductor display device which realizes low power consumption and high reliability. In the active matrix type semiconductor display device of the present invention, a counter electrode is divided into two, different potentials are applied to the two counter electrodes, respectively and inversion driving is carried out each other. Since a potential of an image signal can be made low by doing so, it is possible to lower a voltage necessary for operation of a driver circuit. As a result, it is possible to realize improvement of reliability of an element such as a TFT and reduction of consumed electric power. Moreover, since it is possible to lower a voltage of a timing pulse supplied by the driver circuit, a booster circuit can be omitted, and reduction of an area of the driver circuit can be realized. <IMAGE>

IPC 1-7

**G09G 3/36**; **G09G 3/30**; **G09G 3/32**

IPC 8 full level

**G09G 3/32** (2006.01); **G09G 3/36** (2006.01)

CPC (source: EP US)

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Citation (search report)

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DOCDB simple family (publication)

**EP 1003151 A2 20000524**; **EP 1003151 A3 20011121**; **EP 1003151 B1 20130821**; EP 2290643 A1 20110302; US 2003064552 A1 20030403; US 2004115851 A1 20040617; US 2007166860 A1 20070719; US 6489952 B1 20021203; US 6635505 B2 20031021; US 7198967 B2 20070403; US 7544981 B2 20090609

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**EP 99122790 A 19991116**; EP 10010384 A 19991116; US 29588602 A 20021118; US 43843299 A 19991112; US 61885003 A 20030715; US 71593807 A 20070309